

N-Channel Enhancement Mode MOSFET

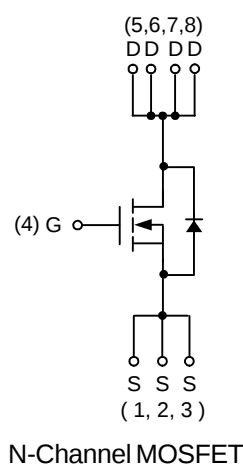
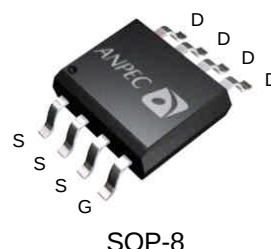
Features

- 30V/11A,
 $R_{DS(ON)} = 9.5m\Omega(Typ.) @ V_{GS} = 10V$
 $R_{DS(ON)} = 13.5m\Omega(Typ.) @ V_{GS} = 4.5V$
- Super High Dense Cell Design
- Avalanche Rated
- Reliable and Rugged
- Lead Free and Green Devices Available
 (RoHS Compliant)

Applications

- Power Management in Notebook Computer,
 and DC-DC Converters in Networking Systems.

Pin Description



Ordering and Marking Information

APM4826 □□-□□ □ Assembly Material Handling Code Temperature Range Package Code	Package Code K : SOP-8 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel Assembly Material G : Halogen and Lead Free Device
APM4826 K : APM4826 XXXXX	XXXXX - Date Code

Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. ANPEC defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 20	
I_D^a	Continuous Drain Current ($V_{GS}=10\text{V}$)	$T_A=25^\circ\text{C}$	A
		$T_A=70^\circ\text{C}$	
I_{DM}^a	300 μs Pulsed Drain Current ($V_{GS}=10\text{V}$)	40	A
I_S^a	Diode Continuous Forward Current	3	
I_{AR}^b	Avalanche Current	22.5	A
E_{AR}^b	Repetitive Avalanche Energy ($L=0.3\text{mH}$)	75	mJ
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	
P_D^a	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	W
		$T_A=70^\circ\text{C}$	
$R_{\theta JA}^{a,c}$	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	$^\circ\text{C/W}$
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	Steady State	$^\circ\text{C/W}$

Note a : Surface Mounted on 1in^2 pad area, $t \leq 10\text{sec}$.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^\circ\text{C}$).

Note c : Maximum under Steady State conditions is 75°C/W .

Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	APM4826K			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.3	1.8	2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^e	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =12A	-	9.5	12	mΩ
		V _{GS} =4.5V, I _{DS} =9A	-	13.5	18	
Diode Characteristics						
V _{SD} ^e	Diode Forward Voltage	I _{SD} =3A, V _{GS} =0V	-	0.75	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =12A, dI _{SD} /dt=100A/μs	-	18	-	ns
Q _{rr}	Reverse Recovery Charge		-	11	-	nC

Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

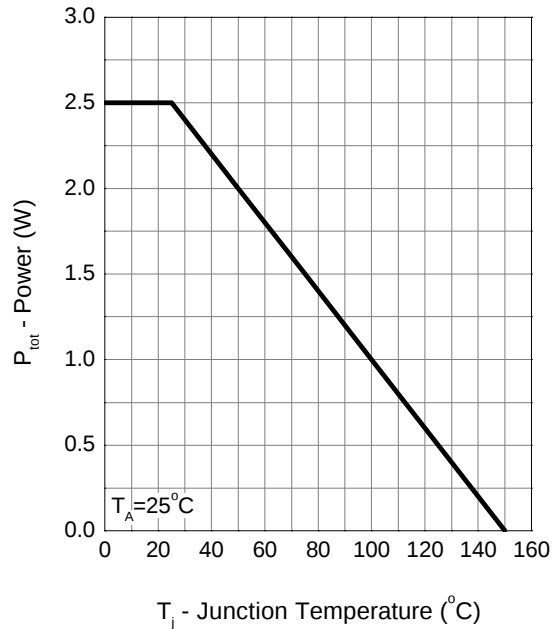
Symbol	Parameter	Test Conditions	APM4826K			Unit
			Min.	Typ.	Max.	
Dynamic Characteristics ^f						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	1	1.7	3	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz	-	1150	1400	pF
C _{oss}	Output Capacitance		-	170	-	
C _{rss}	Reverse Transfer Capacitance		-	135	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	10	19	ns
t _r	Turn-on Rise Time		-	12	23	
t _{d(OFF)}	Turn-off Delay Time		-	30	55	
t _f	Turn-off Fall Time		-	7	14	
Gate Charge Characteristics ^f						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =12A	-	25.3	35	nC
Q _{gs}	Gate-Source Charge		-	3.5	-	
Q _{gd}	Gate-Drain Charge		-	6.5	-	

Note e : Pulse test ; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

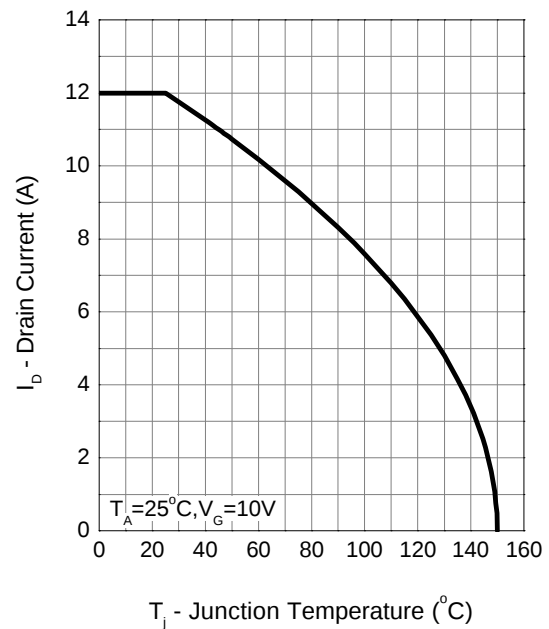
Note f : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

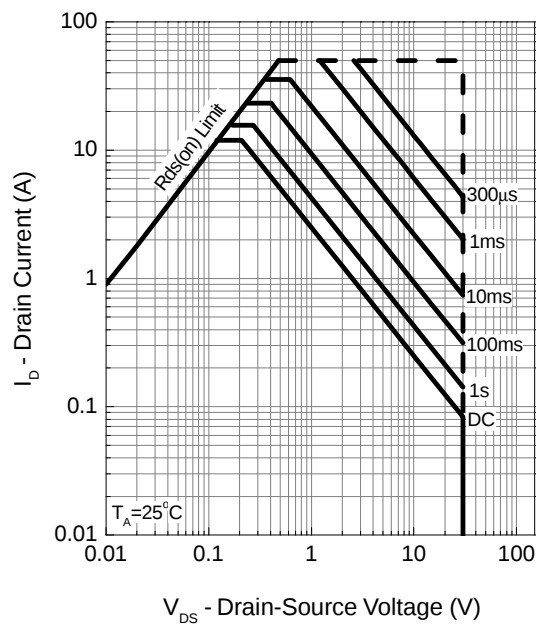
Power Dissipation



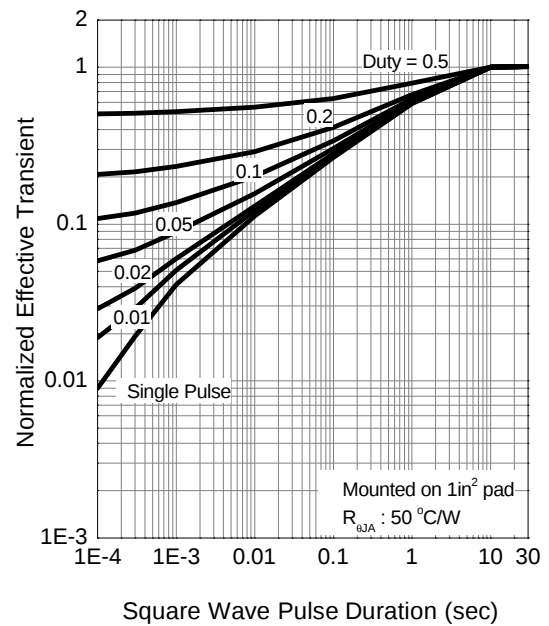
Drain Current



Safe Operation Area

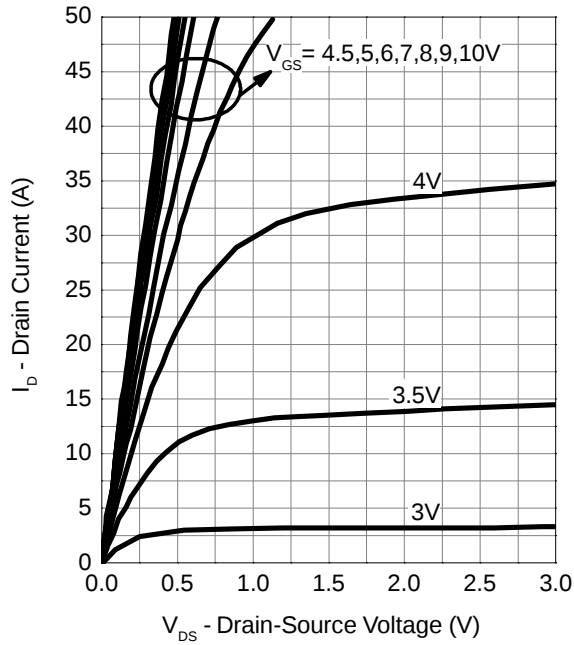


Thermal Transient Impedance

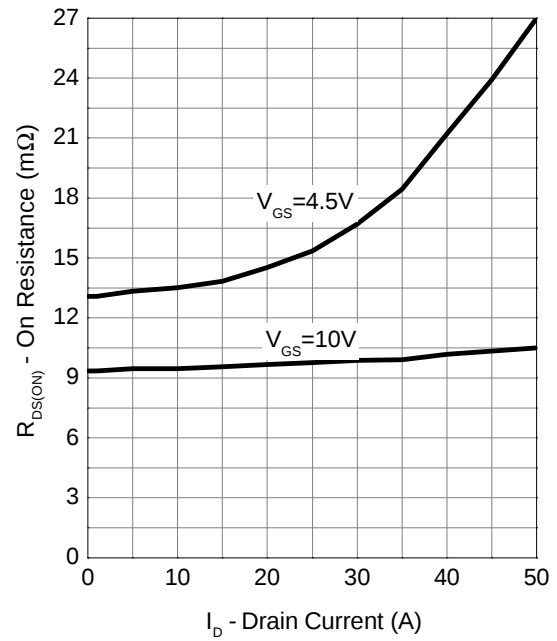


Typical Operating Characteristics (Cont.)

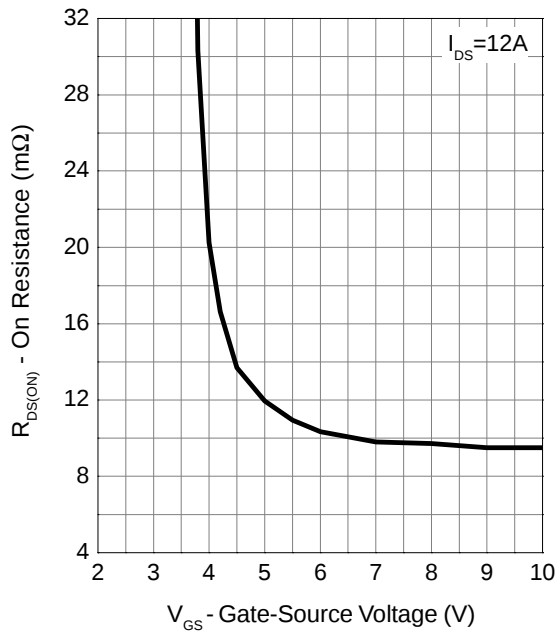
Output Characteristics



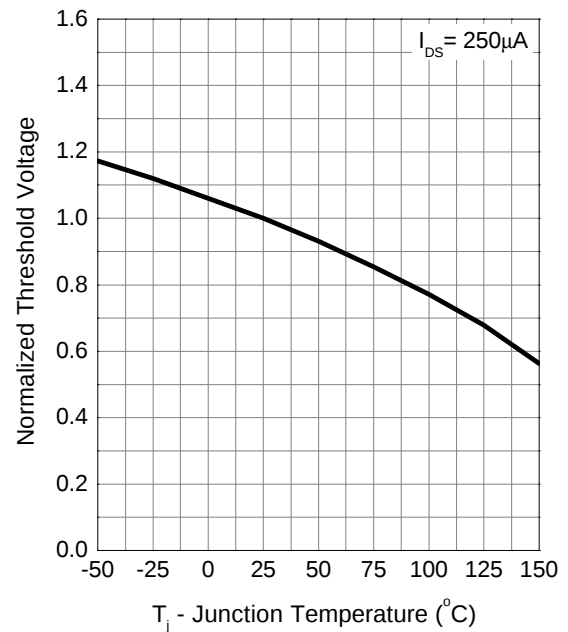
Drain-Source On Resistance



Gate-Source On Resistance

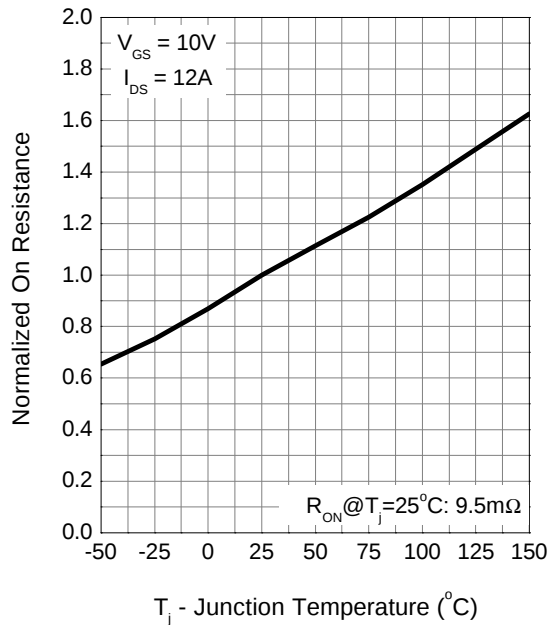


Gate Threshold Voltage

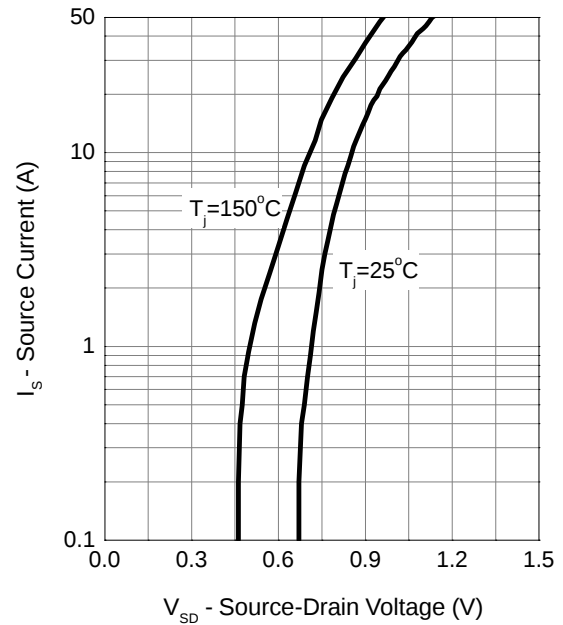


Typical Operating Characteristics (Cont.)

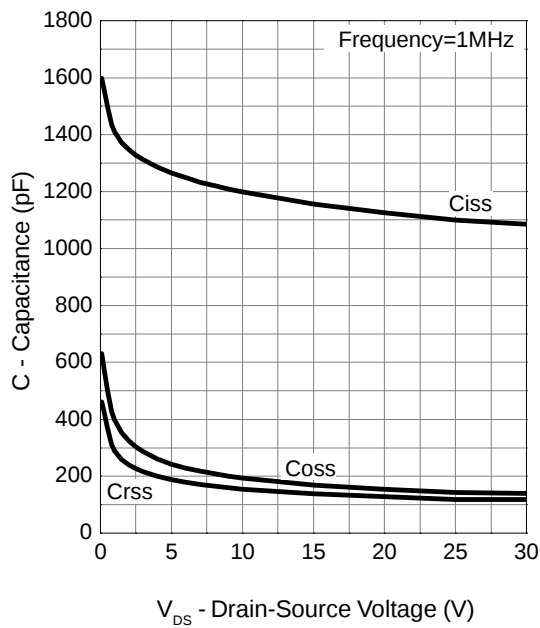
Drain-Source On Resistance



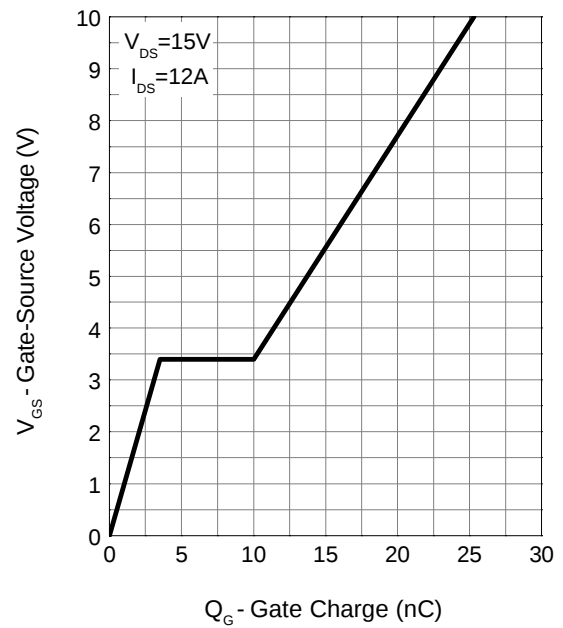
Source-Drain Diode Forward



Capacitance

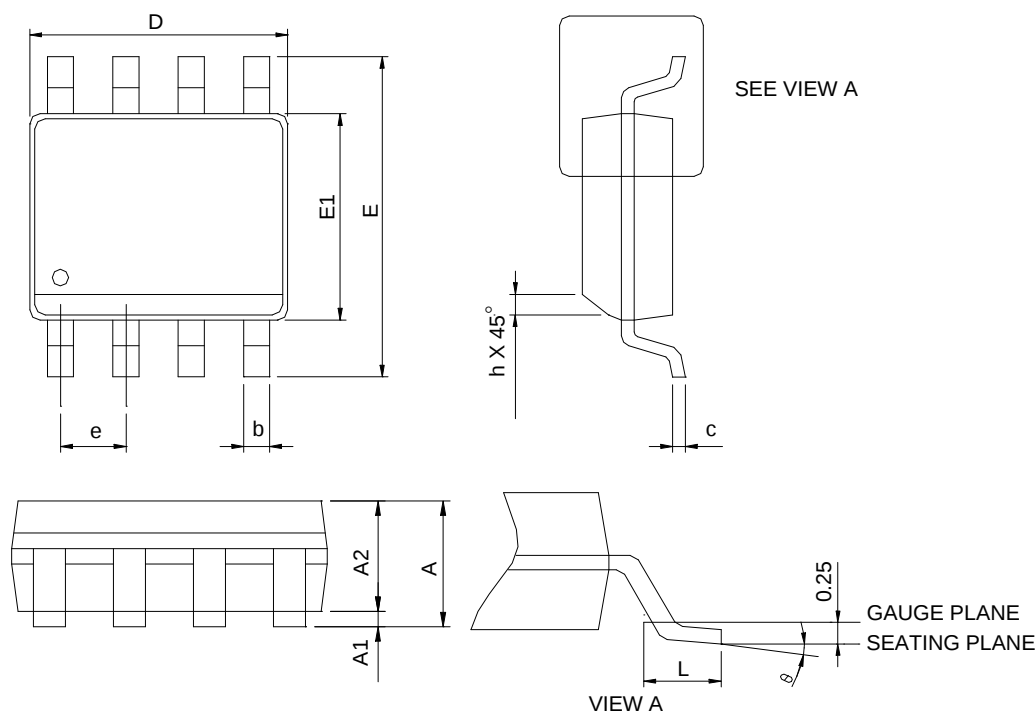


Gate Charge



Package Information

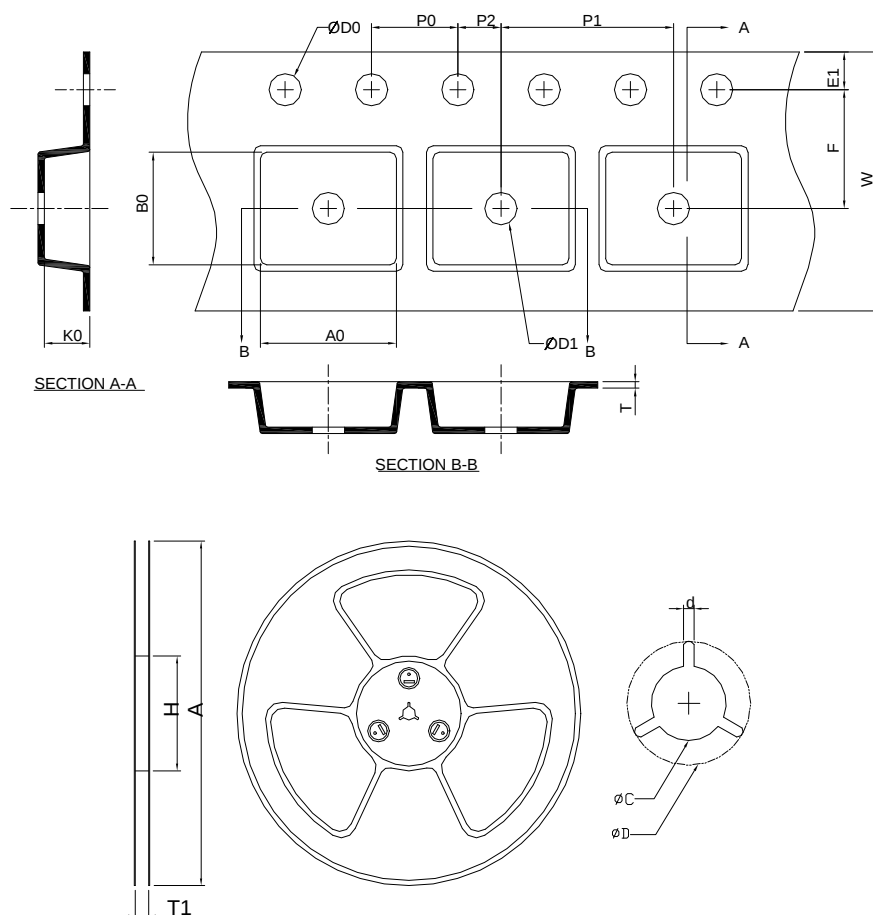
SOP-8



SYMBOL	SOP-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A		1.75		0.069
A1	0.10	0.25	0.004	0.010
A2	1.25		0.049	
b	0.31	0.51	0.012	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°

- Note: 1. Follow JEDEC MS-012 AA.
 2. Dimension "D" does not include mold flash, protrusions or gate burrs.
 Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.
 3. Dimension "E" does not include inter-lead flash or protrusions.
 Inter-lead flash and protrusions shall not exceed 10 mil per side.

Carrier Tape & Reel Dimensions



Application	A	H	T1	C	d	D	W	E1	F
SOP-8	330.0 $\pm$ 2.00	50 MIN.	12.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0 $\pm$ 0.30	1.75 $\pm$ 0.10	5.5 $\pm$ 0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0 $\pm$ 0.10	8.0 $\pm$ 0.10	2.0 $\pm$ 0.05	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	6.40 $\pm$ 0.20	5.20 $\pm$ 0.20	2.10 $\pm$ 0.20

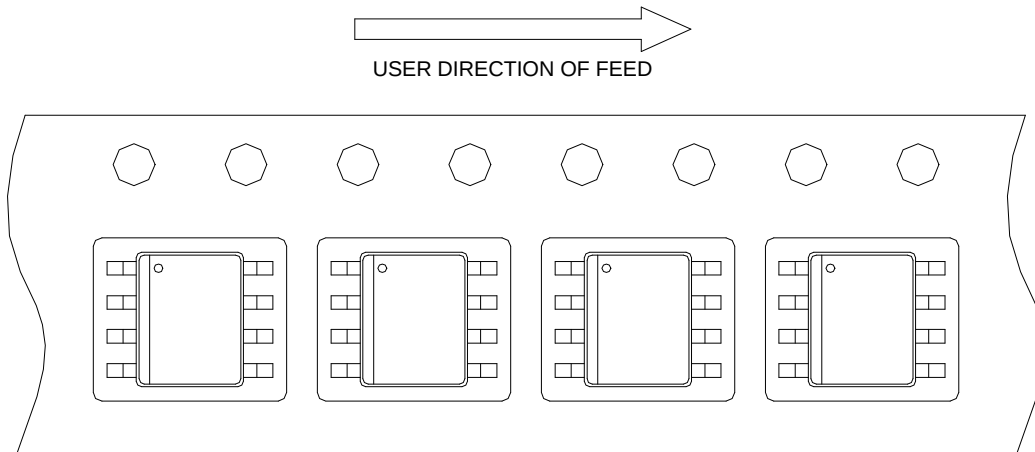
(mm)

Devices Per Unit

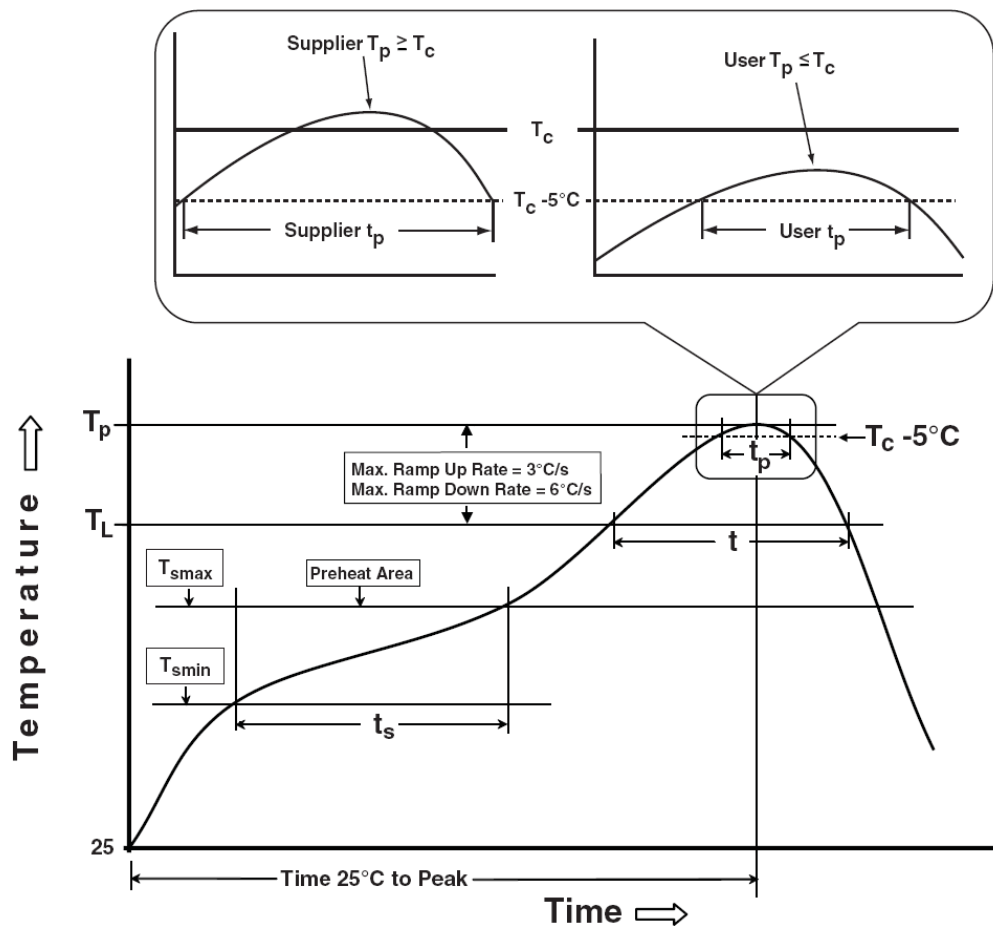
Package Type	Unit	Quantity
SOP-8	Tape & Reel	2500

Taping Direction Information

SOP-8



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HOLT	JESD-22, A108	1000 Hrs, Bias @ 125°C
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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